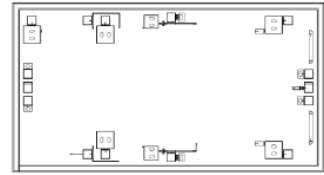


AMT1113
9 – 19GHz Power Amplifier Chip



Key Features :

- Frequency range : 9 – 19GHz
- Typical small signal gain : 26dB
- Typical output power : 35dBm
- Voltage bias : Vd = 8V, Vg = -0.7V
- Chip dimensions : 3.6mm x 1.9mm x 0.1mm
- Applications : wireless communication, transceiver module, radio telecommunication etc.

Description :

AMT1113 chip is designed by Gallium Arsenide (GaAs) pHEMT process, a high performance 9 - 19GHz power amplifier, it uses dual voltage operation, with drain voltage Vd at 8.0V, it offers around 26dB linear gain, and 35dBm saturated output power. This chip is designed with ground through metal vias on the back technology. All chip products are 100% RF tested.

Absolute Maximum Ratings (Ta = 25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	+11V	
Pin	Input Signal Power	15dBm	
Tch	Operating Temperature	-55 ~ +125°C	
Tm	Sintering Temperature	310°C	30s, N ₂ protection
Tstg	Storage Temperature	-65 ~ +150°C	

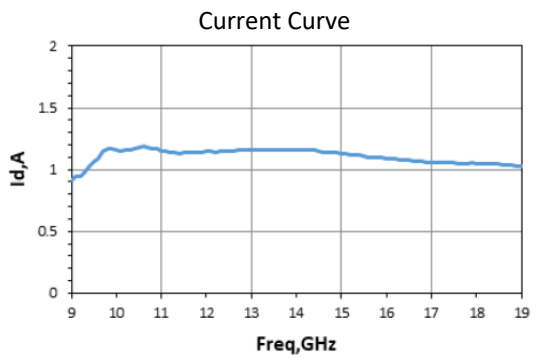
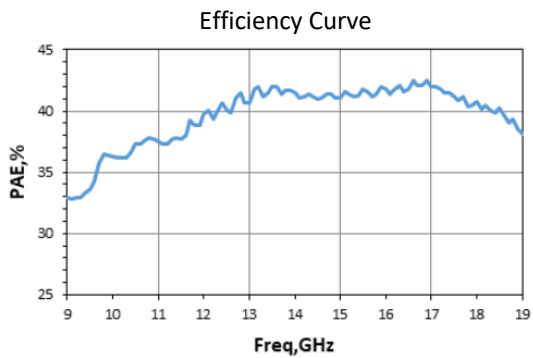
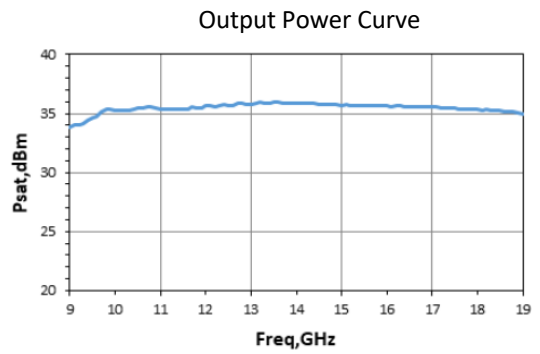
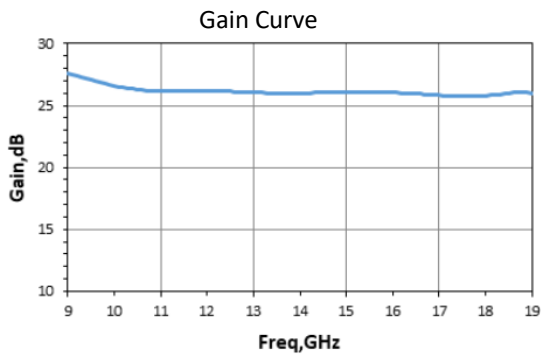
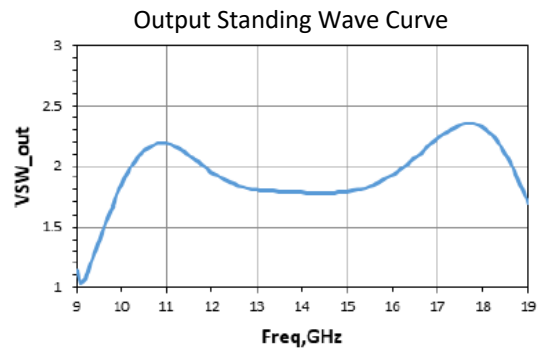
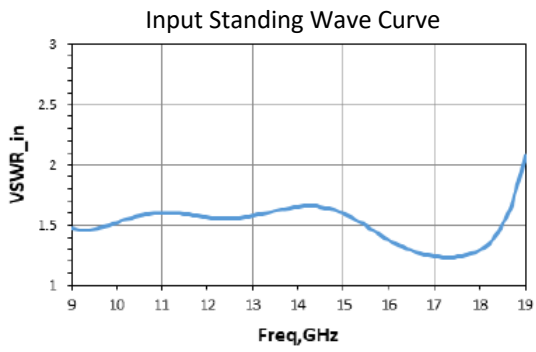
[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

Electrical Characteristics (Ta = 25°C)

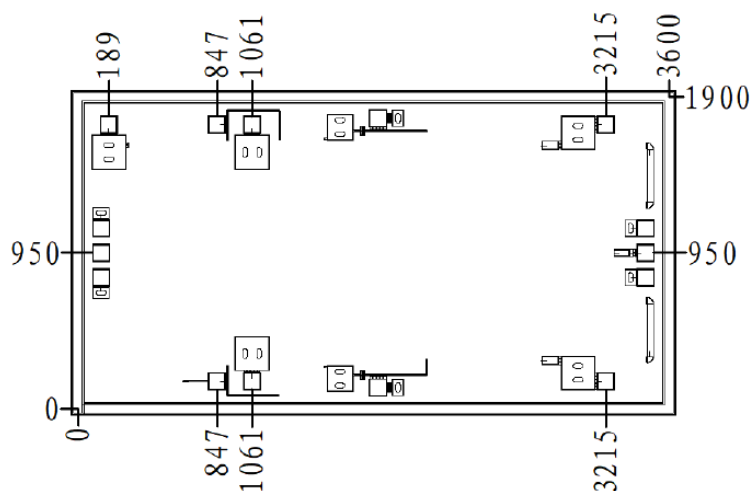
Symbol	Parameter	Test Condition	Value			Unit
			Min	Typical	Max	
G	Small Signal Gain	Vd = 8V Vg = -0.7V F : 9 ~ 19GHz	25.5	26	27.5	dB
Id	Operating Current		-	1.15	-	A
VSWR_in	Input SW		-	1.6	-	
VSWR_out	Output SW		-	2.3	-	
Gp	Power Gain		-	23.5	-	dB
Po(sat)	Saturated Output Power		-	35	-	dBm
PAE	Efficiency		-	38	-	%

Note, no CW operation.

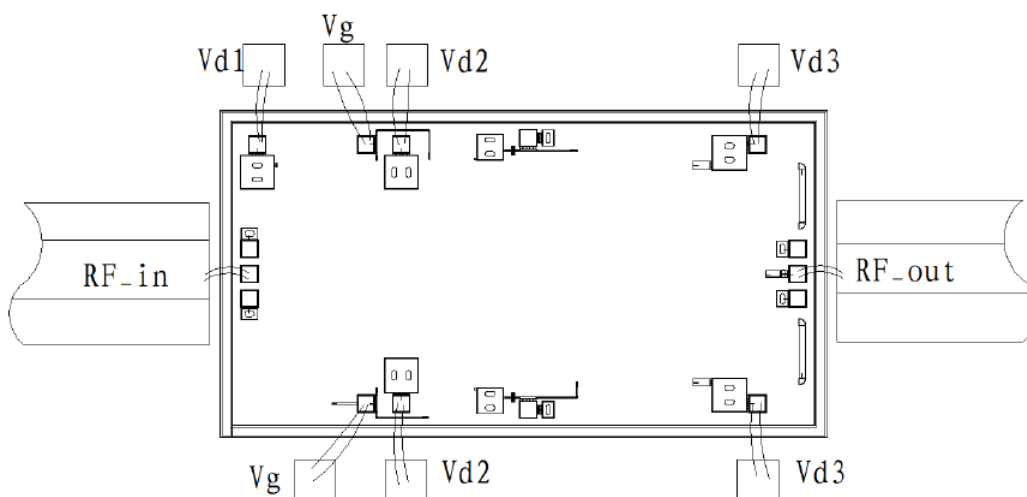
Typical Performance



Chip Dimensions (Unit : μm)



Chip Layout Diagram



Please see Appendix A for details.